



### Vishay Semiconductors

# Hyperfast Rectifier, 8 A FRED Pt®





D-PAK (TO-252AA)

PRODUCT SUMMARY							
Package	D-PAK (TO-252AA)						
I <sub>F(AV)</sub>	8 A						
V <sub>R</sub>	600 V						
V <sub>F</sub> at I <sub>F</sub>	3.0 V						
t <sub>rr</sub> (typ.)	15 ns						
T <sub>J</sub> max.	175 °C						
Diode variation	Single die						

### **FEATURES**







· Low forward voltage drop

· Low leakage current

 Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C



• Halogen-free according to IEC 61249-2-21 definition







#### HALOGEN FREE

#### **DESCRIPTION/APPLICATIONS**

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS inverters or as freewheeling diodes. Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Peak repetitive reverse voltage	$V_{RRM}$		600	V				
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 140 °C	8					
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	90	Α				
Peak repetitive forward current	I <sub>FM</sub>	T <sub>C</sub> = 140 °C, f = 20 kHz, d = 50 %	16					
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		- 65 to 175	°C				

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)									
PARAMETER	METER SYMBOL TEST CONDITIONS			TYP.	MAX.	UNITS			
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	Ι <sub>R</sub> = 100 μΑ	600	-	-				
Forward voltage	V	I <sub>F</sub> = 8 A	-	2.3	3.0	V			
	V <sub>F</sub>	I <sub>F</sub> = 8 A, T <sub>J</sub> = 150 °C	-	1.4	1.7				
Deverage legisers assured		V <sub>R</sub> = V <sub>R</sub> rated	-	-	50				
Reverse leakage current	I <sub>R</sub>	$T_J = 150 ^{\circ}\text{C},  V_R = V_R  \text{rated}$		500	μA				
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 600 V	-	7	-	pF			
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8	-	nH			

# VS-8EWX06FN-M3

#### Vishay Semiconductors Hyperfast Rectifier, 8 A FRED Pt®



<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS			
		$I_F = 1 A, dI_F/dt = 10$	$I_F = 1 \text{ A, } dI_F/dt = 100 \text{ A/}\mu\text{s, } V_R = 30 \text{ V}$		15	19			
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	17	-	ns - A		
		T <sub>J</sub> = 125 °C	I <sub>F</sub> = 8 A dI <sub>F</sub> /dt = 200 A/µs V <sub>B</sub> = 390 V	-	40	-			
Peak recovery current	1	T <sub>J</sub> = 25 °C		-	2.5	-			
	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C		-	4.5	-			
Reverse recovery charge	0	T <sub>J</sub> = 25 °C		-	22	-	nC		
	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	70	-			

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 65	-	175	°C				
Thermal resistance, junction to case per leg	$R_{thJC}$		-	1.8	2.2	°C/W				
Approximate weight				0.3		g				
Approximate weight				0.01		OZ.				
Marking device		Case style D-PAK (TO-252AA)	8EWX06FN							





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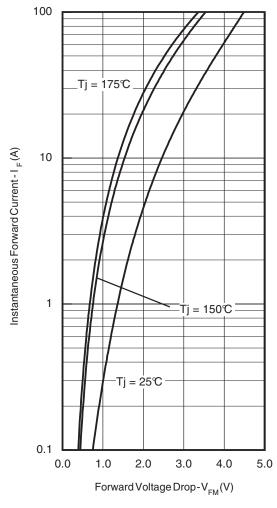


Fig. 1 - Typical Forward Voltage Drop Characteristics

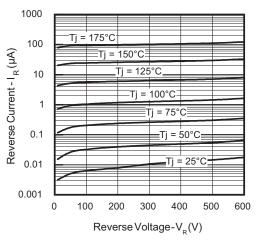


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

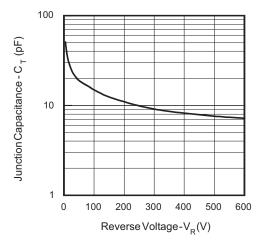


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

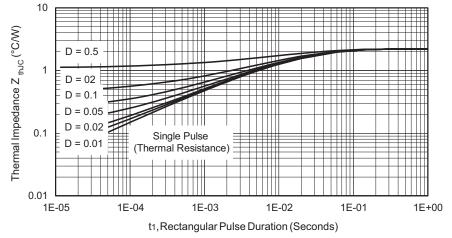


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

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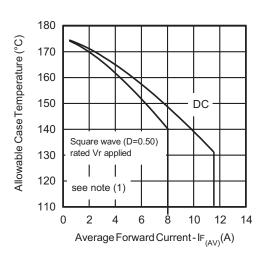


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

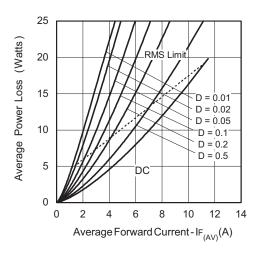


Fig. 6 - Forward Power Loss Characteristics

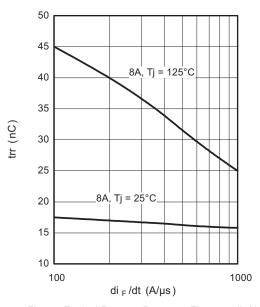


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

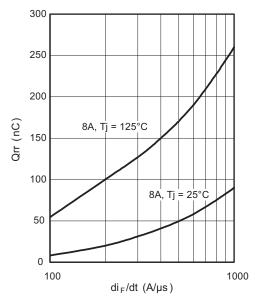


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

<sup>(1)</sup> Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ; Pd = Forward power loss =  $I_{F(AV)} \times V_{FM}$  at  $(I_{F(AV)}/D)$  (see fig. 6); Pd<sub>REV</sub> = Inverse power loss =  $V_{R1} \times I_R (1 - D)$ ;  $I_R$  at  $V_{R1}$  = Rated  $V_R$ 



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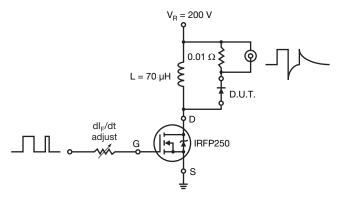
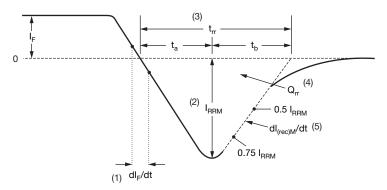


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1)  $dI_F/dt$  rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3)  $t_{\rm rr}$  reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.
- (4) Q<sub>rr</sub> area under curve defined by t<sub>rr</sub> and I<sub>RRM</sub>

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5)  $dl_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

Fig. 10 - Reverse Recovery Waveform and Definitions

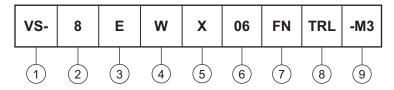
### VS-8EWX06FN-M3

#### Vishay Semiconductors Hyperfast Rectifier, 8 A FRED Pt®



### **ORDERING INFORMATION TABLE**

**Device code** 



Vishay Semiconductors product

Current rating (8 = 8 A)

Circuit configuration:

E = Single diode

Package identifier:

W = D-PAK

X = Hyperfast recovery time

Voltage rating (06 = 600 V)

FN = TO-252AA

• None = Tube

• TR = Tape and reel

• TRL = Tape and reel (left oriented)

• TRR = Tape and reel (right oriented)

9 Environmental digit:

-M3 = Halogen-free, RoHS compliant and terminations lead (Pb)-free

ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-8EWX06FN-M3	75	3000	Antistatic plastic tube					
VS-8EWX06FNTR-M3	2000	2000	13" diameter reel					
VS-8EWX06FNTRL-M3	3000	3000	13" diameter reel					
VS-8EWX06FNTRR-M3	3000	3000	13" diameter reel					

LINKS TO RELATED DOCUMENTS							
Dimensions	www.vishay.com/doc?95016						
Part marking information	www.vishay.com/doc?95176						
Packaging information	www.vishay.com/doc?95033						
SPICE model	www.vishay.com/doc?95374						



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**NOTES** 

3

2

MAX.

0.410

0.070

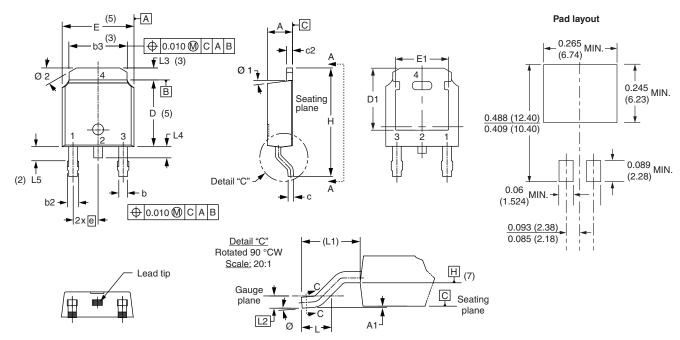
0.050

0.040

0.060

# **D-PAK (TO-252AA)**

#### **DIMENSIONS** in millimeters and inches



Ī	SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES			
	STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STIMBOL	MIN.	MAX.	MIN.	MAX	
ſ	Α	2.18	2.39	0.086	0.094			e 2.29 BSC		0.090	BSC		
ſ	A1	-	0.13		0.005			Н	9.40	10.41	0.370	0.41	
Ī	b	0.64	0.89	0.025	0.035			L	1.40	1.78	0.055	0.07	
Ī	b2	0.76	1.14	0.030	0.045			L1	2.74	2.74 BSC		0.108 REF.	
ſ	b3	4.95	5.46	0.195	0.215	3		L2	0.51 BSC		0.020 BSC		
Ī	С	0.46	0.61	0.018	0.024			L3	0.89	1.27	0.035	0.05	
Ī	c2	0.46	0.89	0.018	0.035			L4	-	1.02	-	0.04	
ſ	D	5.97	6.22	0.235	0.245	5		L5	1.14	1.52	0.045	0.06	
Ī	D1	5.21	-	0.205	-	3		Ø	0°	10°	0°	10°	
ſ	Е	6.35	6.73	0.250	0.265	5		Ø1	0°	15°	0°	15°	
Ī	E1	4.32	-	0.170	-	3		Ø2	25°	35°	25°	35°	

### Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- Lead dimension uncontrolled in L5
- Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad
- Section C C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip
- Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- Dimension b1 and c1 applied to base metal only
- (7) Datum A and B to be determined at datum plane H
- Outline conforms to JEDEC outline TO-252AA



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Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

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